

Supplementary Materials: Amorphous InGaZnO Thin Film Transistor Fabricated with Printed Silver Salt Ink Source/Drain Electrodes

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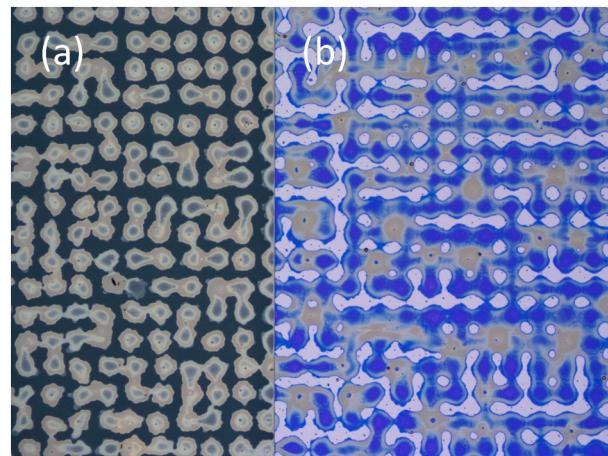


Figure S1. Images of the inkjet printing silver ink on (a) the glass and (b) the Al_2O_3 .

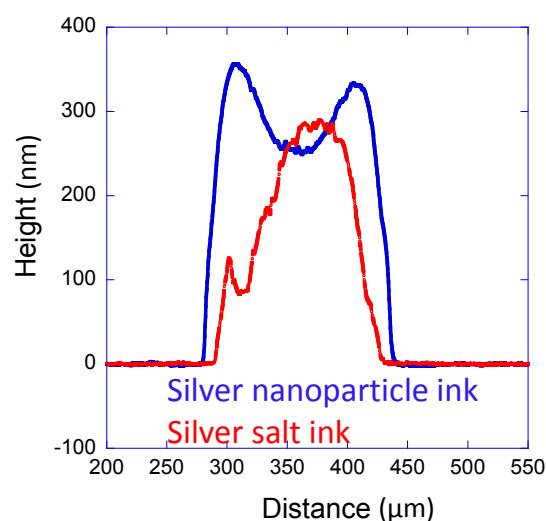


Figure S2. The thickness of the Ag electrodes by using two types of silver ink.

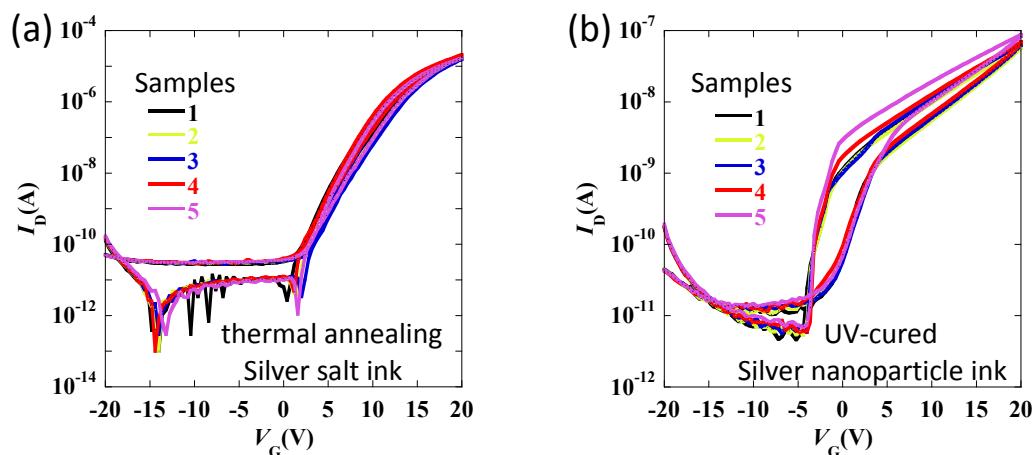


Figure S3. Transfer characteristics curves (I_D - V_G) for devices by using (a) silver salt ink and (b) silver nanoparticle ink.

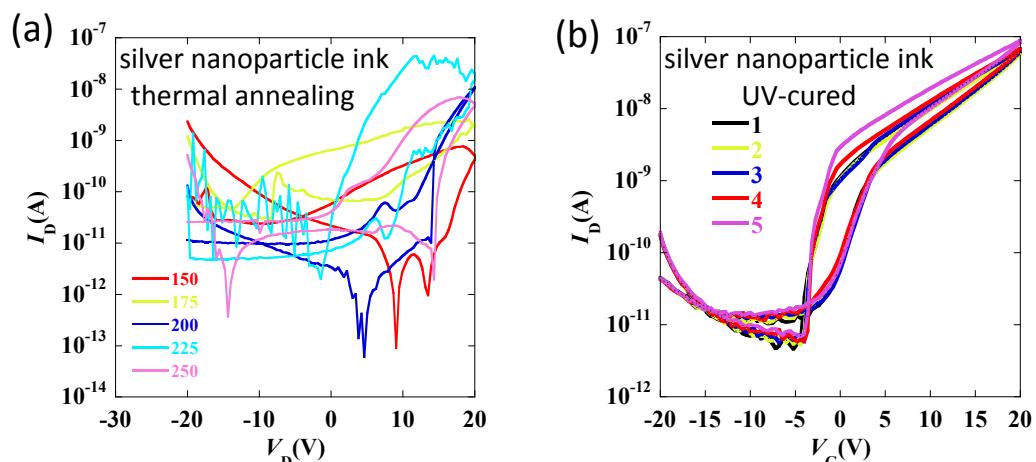


Figure S4. Transfer characteristics curves (I_D - V_G) for devices by using silver nanoparticle ink under (a) thermal annealing and (b) UV-curing.

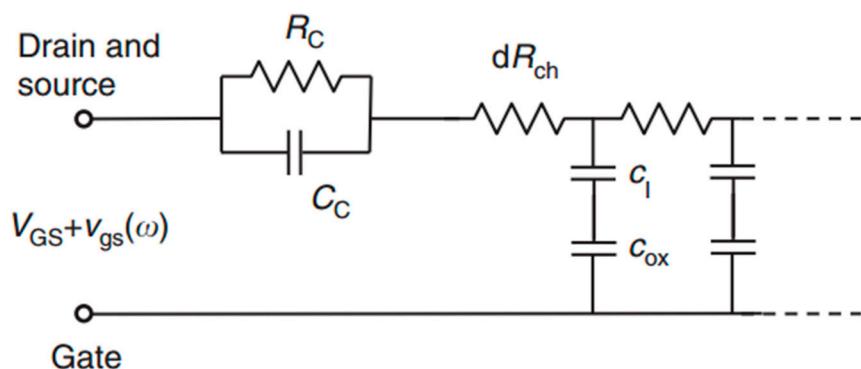


Figure S5. Schematic diagram of circuit for thin film transistor.

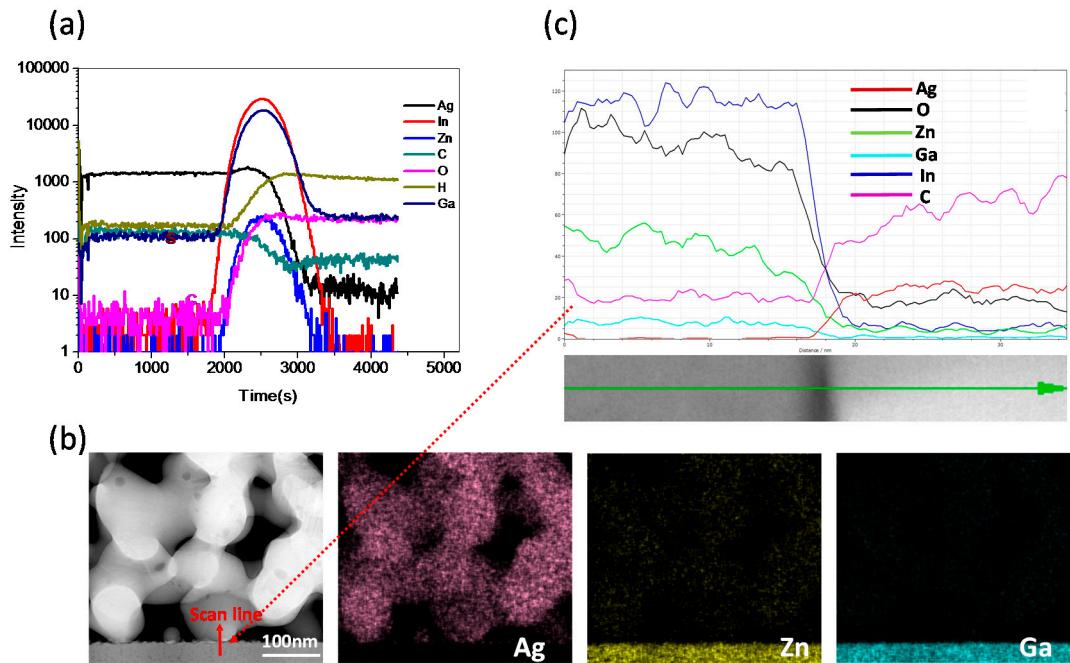


Figure S6. The depth profile of the devices by using (a) silver nanoparticle ink; (b) EDS mapping; and (c) line scanning of the Ag/a-IGZO interface.

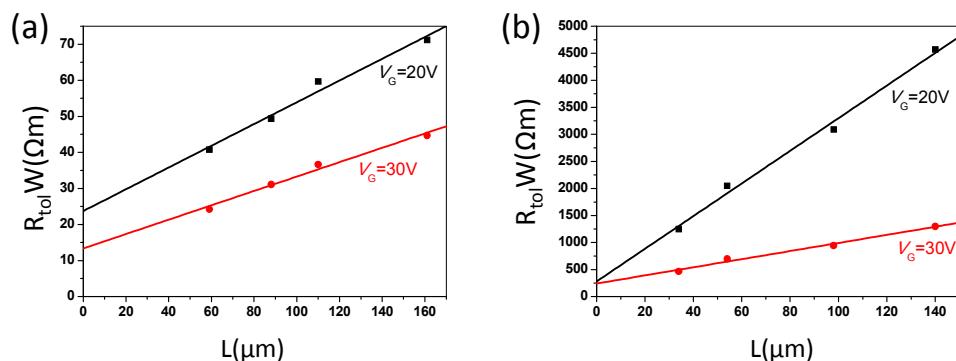


Figure S7. The contact resistance of devices with (a) silver salt ink and (b) silver nanoparticle ink.

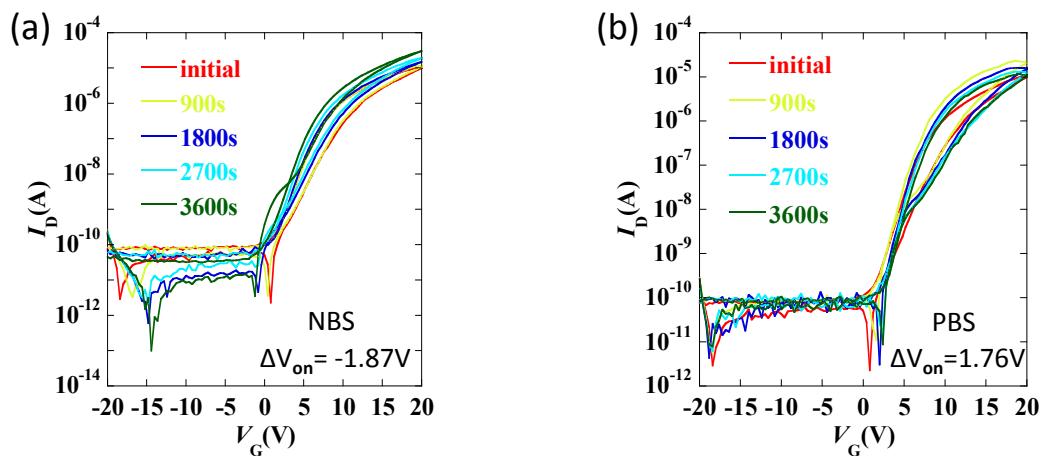


Figure S8. The variations of time-dependent transfer property under (a) positive gate-bias-stress ($V_G=10$ V) and (b) negative gate-bias stress ($V_G=-10$ V).

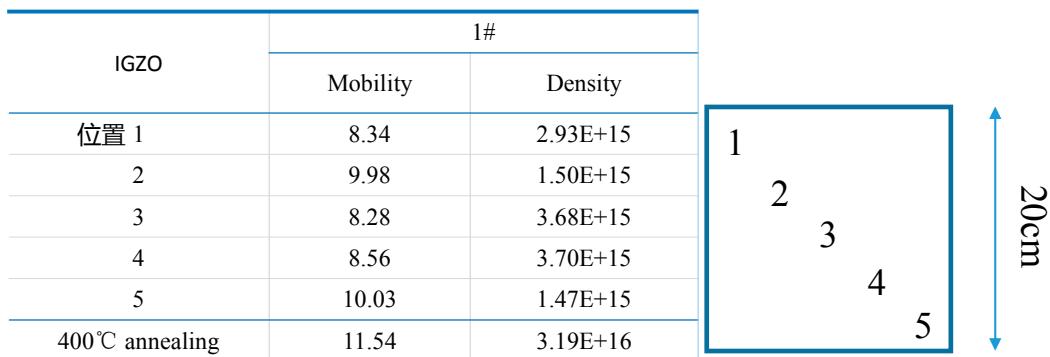


Figure S9. The mobility and the density of the a-IGZO by the Hall measurements

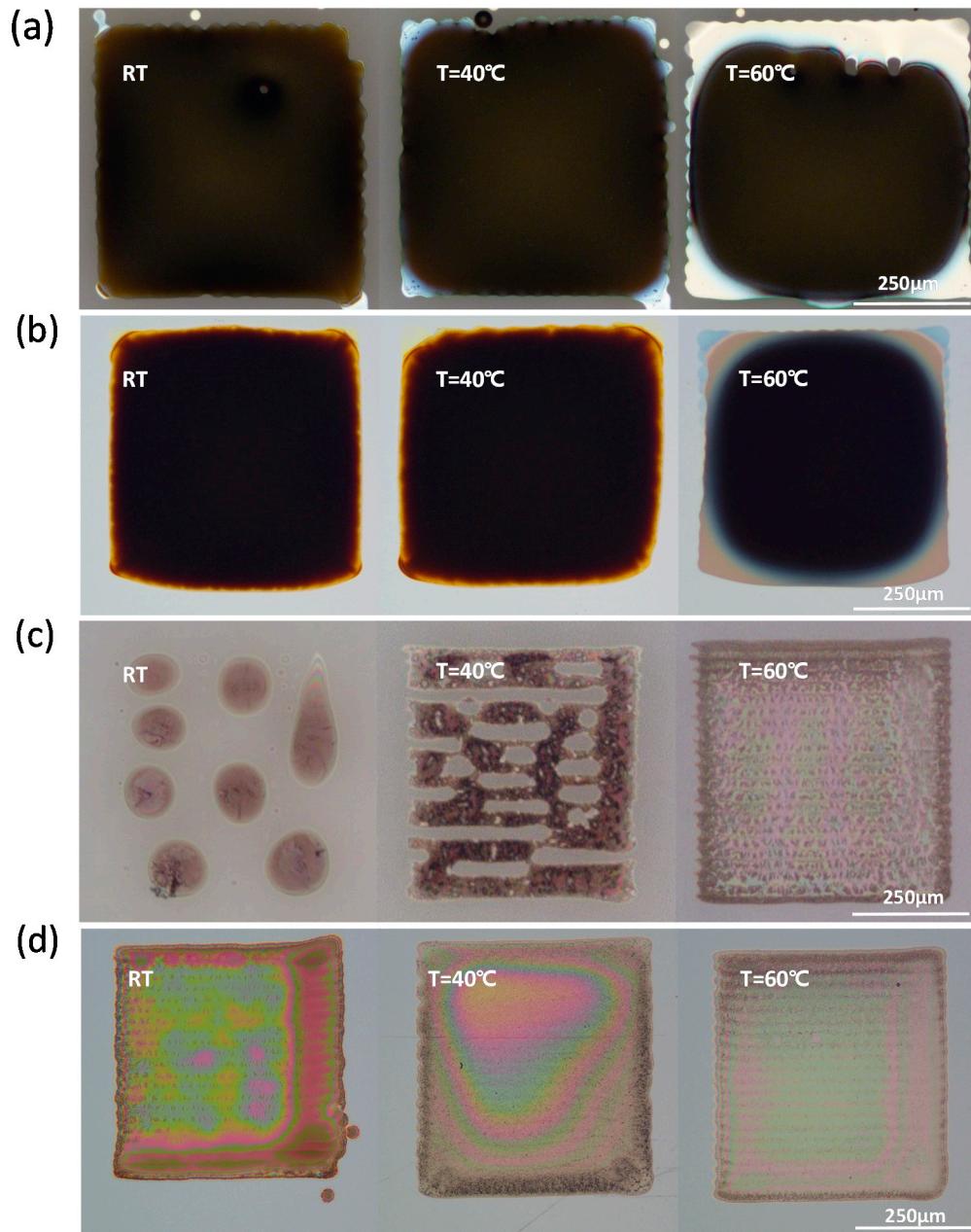


Figure S10. Inkjet printing silver nanoparticle ink film on (a) glass and (b) a-IGZO/Al₂O₃ with substrate temperature of RT, 40°C and 60°C, respectively; Inkjet printing silver salt ink film on (c) glass and (d) a-IGZO/Al₂O₃ with substrate temperature of RT, 40°C and 60°C, respectively.

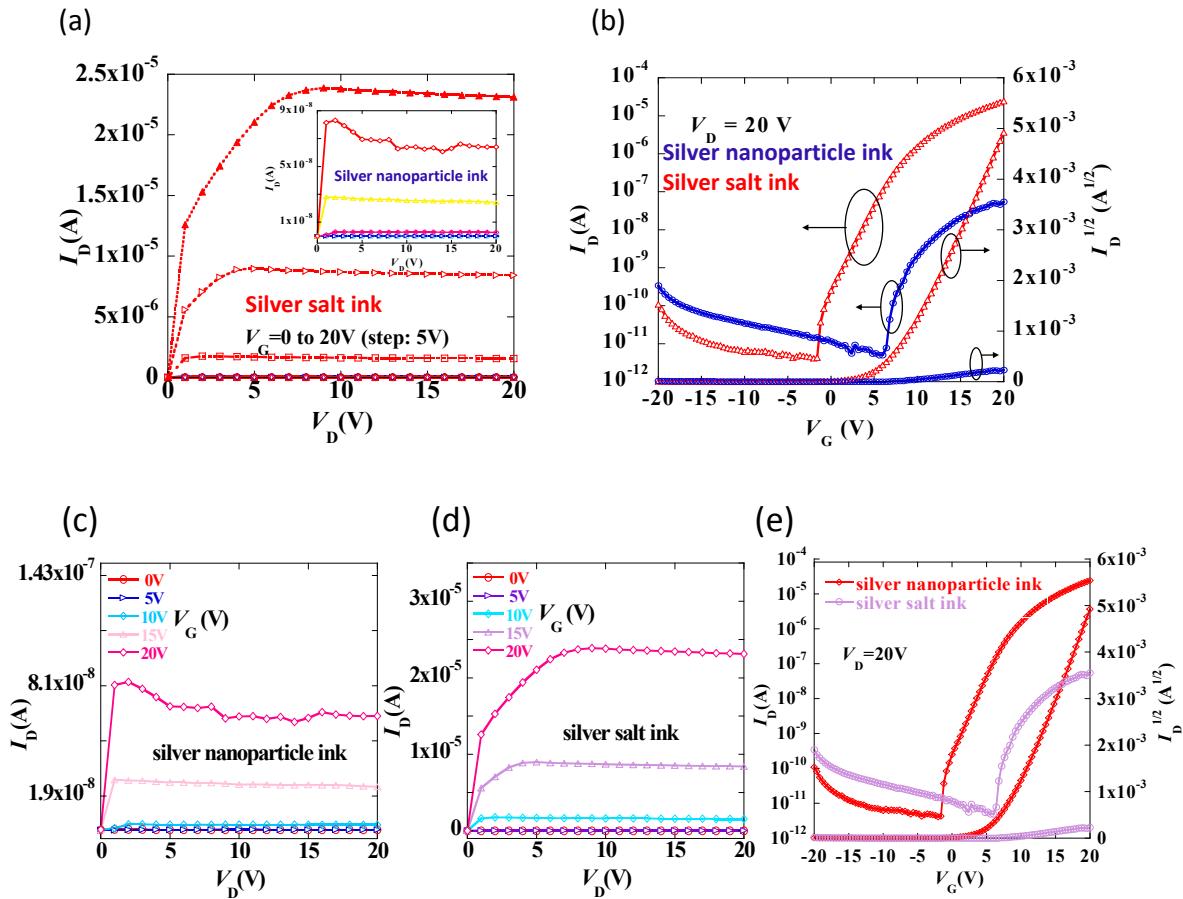


Figure S11. The output characteristic curves (I_D - V_D) and transfer characteristic curves (I_D - V_G) of the devices express through different greyscale.